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# PRECISE SELECTIVE DOPING AND METALLIZATION FOR NEXT-GENERATION PERC TECHNOLOGY

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# AGENDA

- Motivation
  - PERC's roadmap according to ISE
  - ITRPV predictions
- Approach
  - PERC base line
  - Precise, congruent patterning
- Application
  - Selective emitter PERC
  - Bifacial cells
- Conclusions



ITRPV: International Technology Roadmap for Photovoltaic

# Motivation

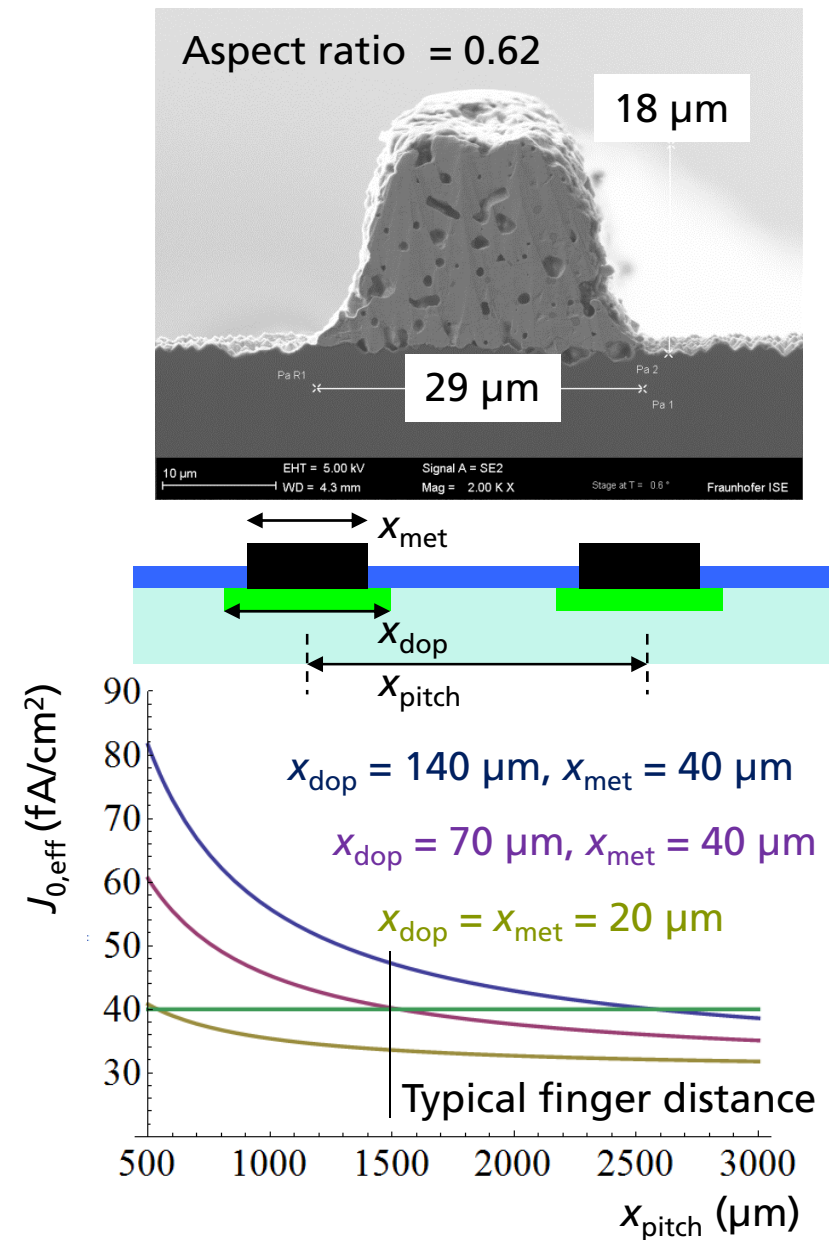
## *PERC's roadmap according to ISE*

- 7-step program to 240 W/m<sup>2</sup> \*
  - 1: Fine, high aspect ratio front contacts
  - **2: No-overlap selective emitters**
  - 3: Low-cost, high quality material
  - 4: Increased productivity
  - **5: Bifaciality**
  - 6: Bifacial shingled cells with passivated edge
  - 7: Introduction of passivated contacts

# Motivation

## *ITRPV predictions for 2029*

- Feature size target  
 **$x_{\text{met}}$  below 20  $\mu\text{m}$**
- Effective dark saturation current density target per side  
 **$J_{0,\text{eff}}$  below 40  $\text{fA}/\text{cm}^2$**
- Precision enables ITRPV predictions
- Max. alignment tolerance of  $\pm 15 \mu\text{m}$



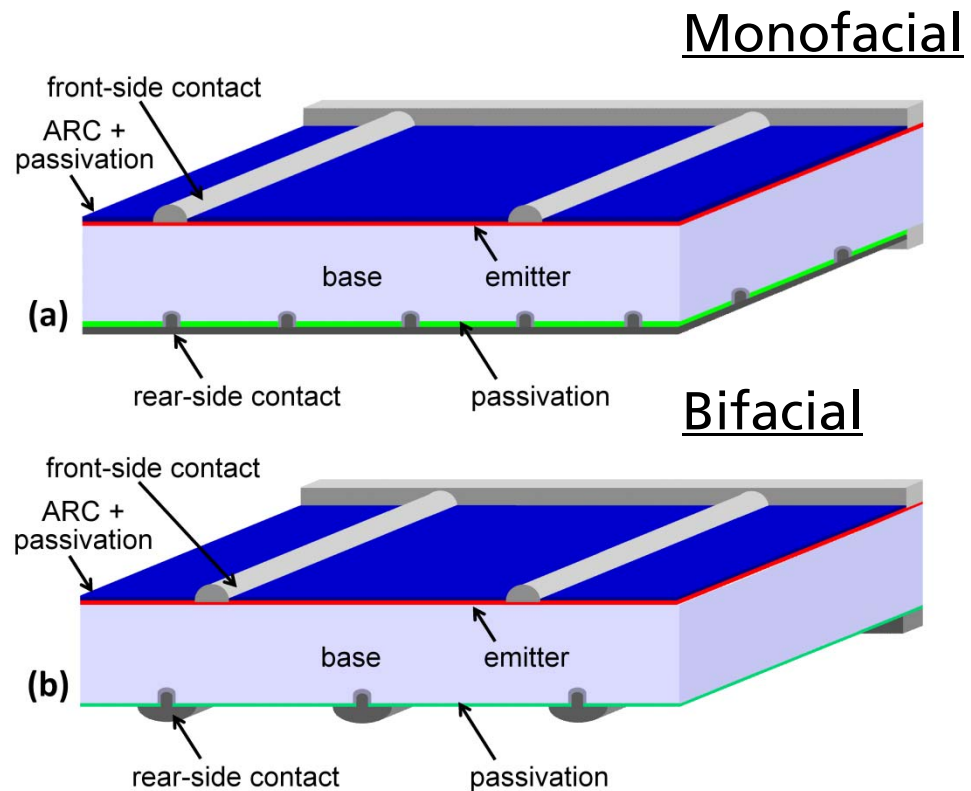
ITRPV, 2018 Results, Tenth Edition, March 2019

# Motivation

## *ITRPV predictions for 2029*

- Bifacial cells enable
  - Collection of light from both solar cell sides
  - Additional **yield by 10 - 40% [1-3]**
- Bifacial cells will gain market share
  - 15% in 2019
  - **60% in 2029**

➤ Even more patterning



[1] L. Podlowski et al., Bifi workshop, 2017;

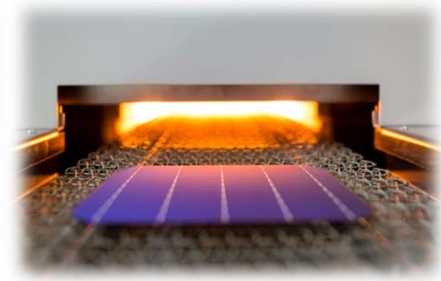
[2] N. Eisenberg, R. Kopecek, V. Fakhfouri et al., PV-tech.org, 2017;

[3] A. Flores et al., Taiyang News, 2017;

# Approach

## *PERC base line process*

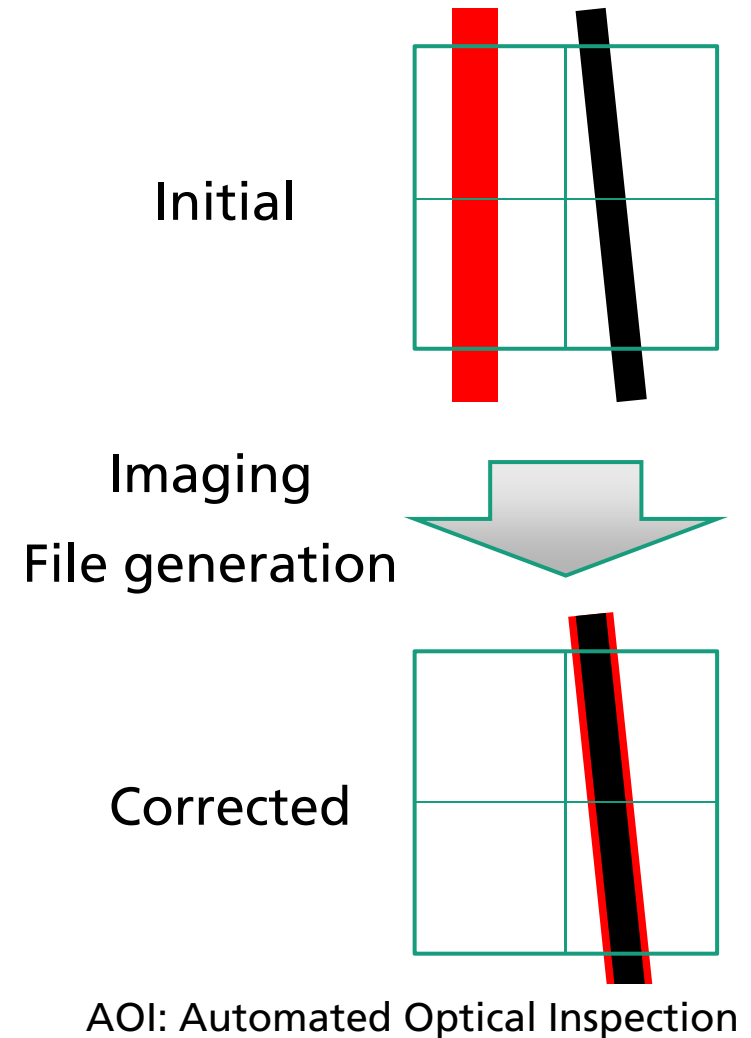
- Industrial PERC solar cells processed in two separate pilot-lines
  - Front-End (no metal)
  - Back-End
- Efficiency of **21.6 %**
- Evaluation of
  - Machines and Components
  - Materials like **solar cell precursors**



# Approach

## *Precise, congruent patterning*

- Digital file generation based on e.g. screen-printed pattern
- Procedure
  - Fabrication of test samples
  - Imaging,  $r_{x,y} = 5 \mu\text{m}$ 
    - Shape determination
    - Offset determination
      - Typ. max. offset  $\pm 50 \mu\text{m}$
  - Shape-congruent file generation incl. Offset (algorithm)
  - Vision: AOI meets file generation

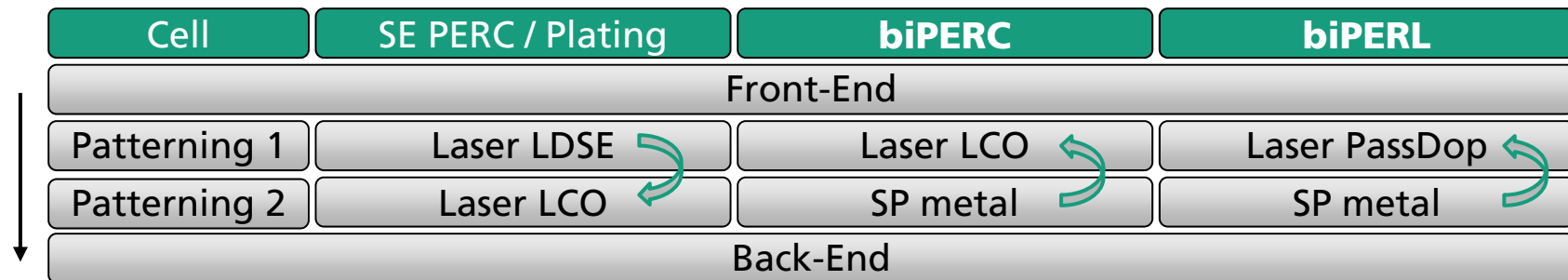




# Approach

## *Industrial application*

- Patterning process 2 and 1 can be adapted to each other
- Patterning process 1 can be adapted to process 2 and the processes are directly in a row
- Potential industrial PERC upgrades



- R&D option: SE PERC; inkjet for ink&etch doping and screen printing for metallization;

LDSE: Laser-diffused sel. Emitter; LCO: Laser contact opening; SP: Screen printing;  
SE: Selective emitter;



# Application I (R&D)

## *Selective emitter PERC*

### Screen-printed metal on ink&etch doping

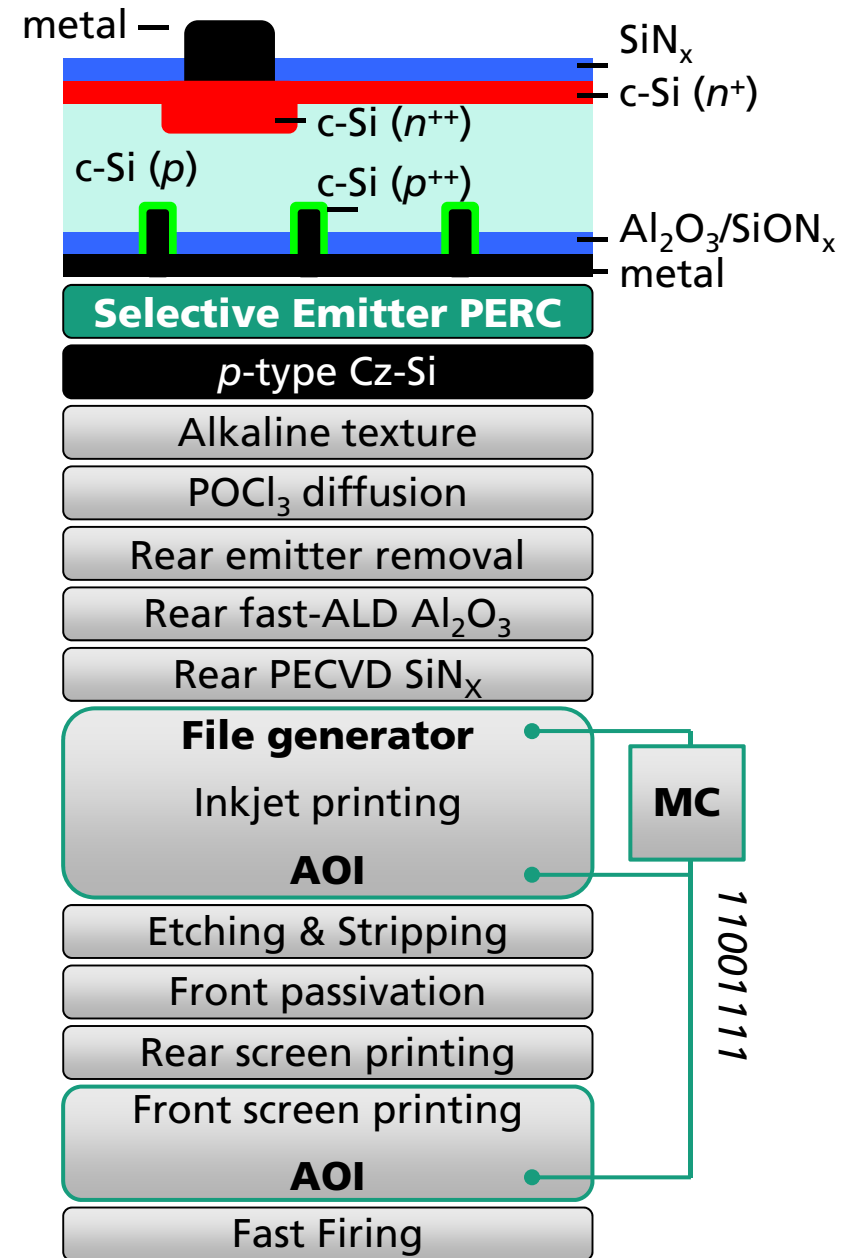


# Selective Emitter PERC

## Patterning

- Doping patterning
  - Diffusion
  - Ink&etch of c-Si ( $n^{++}$ )
- Metal application
  - Screen printing
  - Alternatives at ISE
    - Rotational printing
    - Flexo and Rotational SP
    - Dispensing

MC: Microcontroller

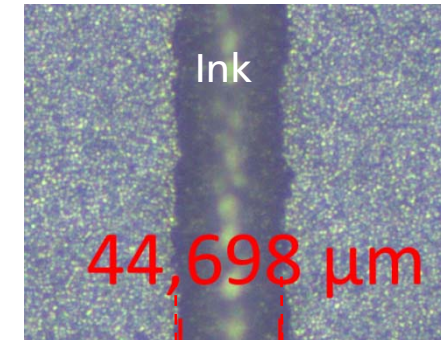


# Selective Emitter PERC

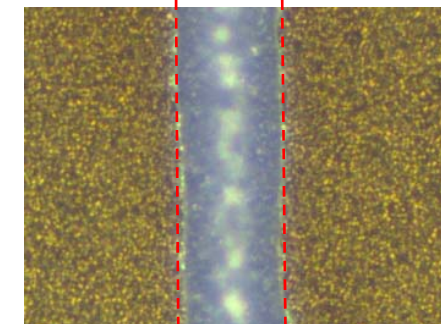
## *Feature size of c-Si( $n^{++}$ )*

- Technique
  - Inkjet of wax
  - Selective etching of silicon
  - Stripping and cleaning
- No underetching detected
- Feature size of c-Si( $n^{++}$ ) equals jetted lines
- Minimum feature size **below 30  $\mu\text{m}$**

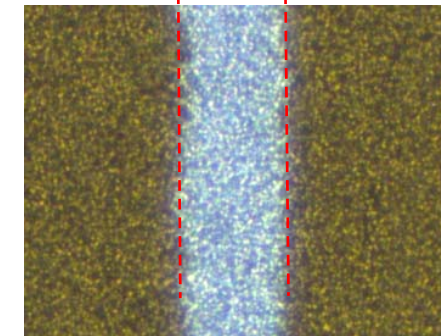
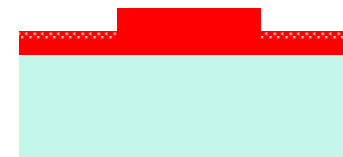
Printing



Etching



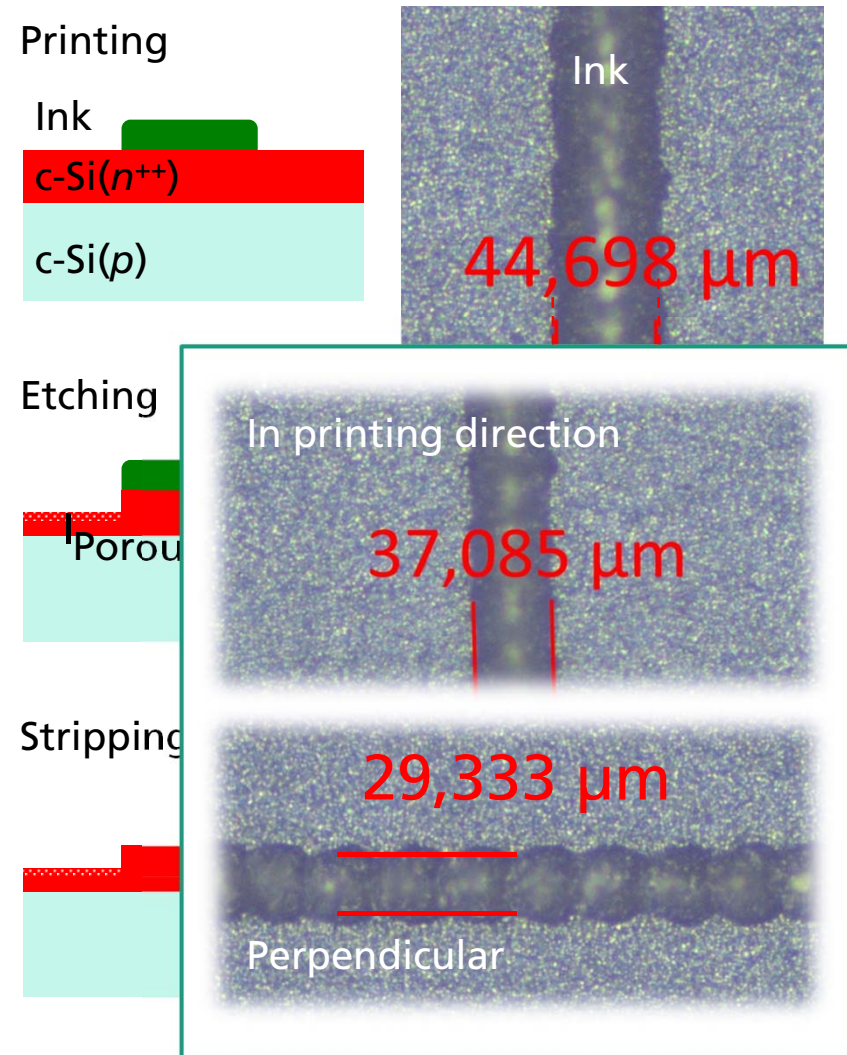
Stripping



# Selective Emitter PERC

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# Selective Emitter PERC

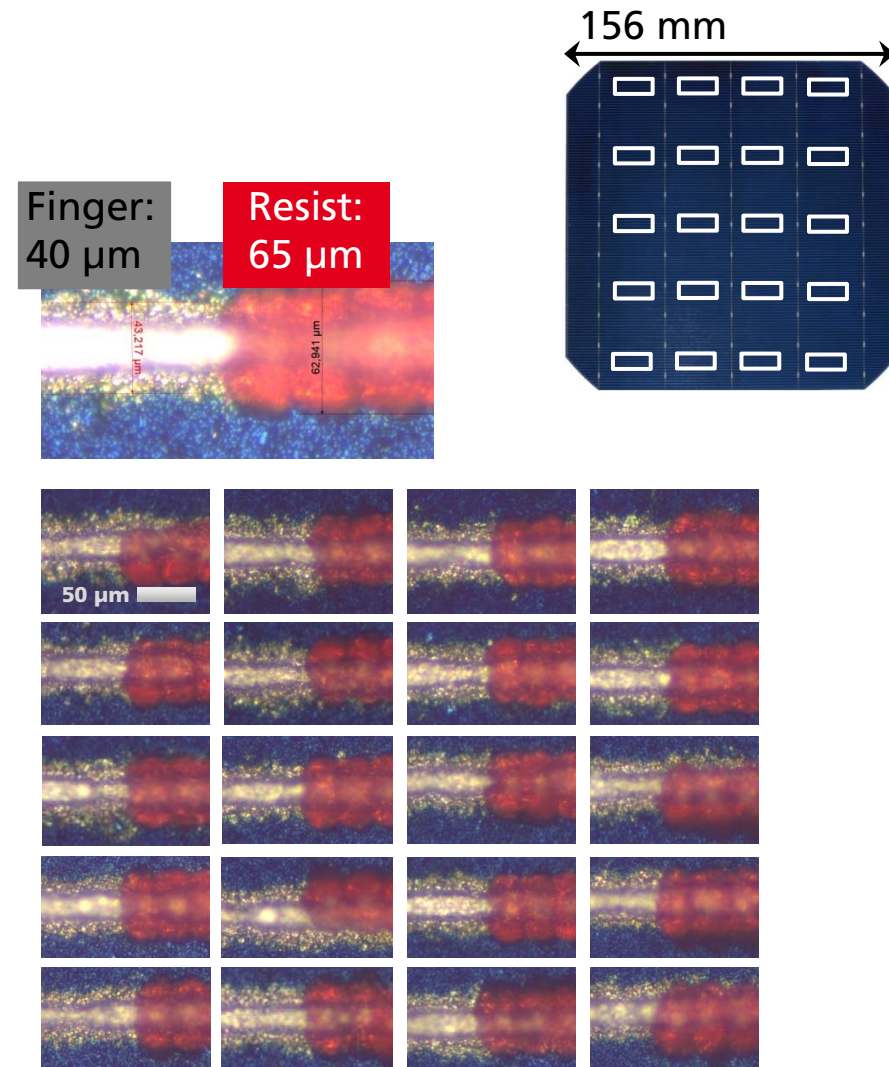
## Alignment precision

### ■ Method

- Screen printing of fingers
- Inkjet printing of **adapted pattern** incl. **interrupted lines** for vizualization
- Microscopy of around 1000 positions per wafer

### ■ Result

- Alignment accuracy **below  $\pm 15 \mu\text{m}$**

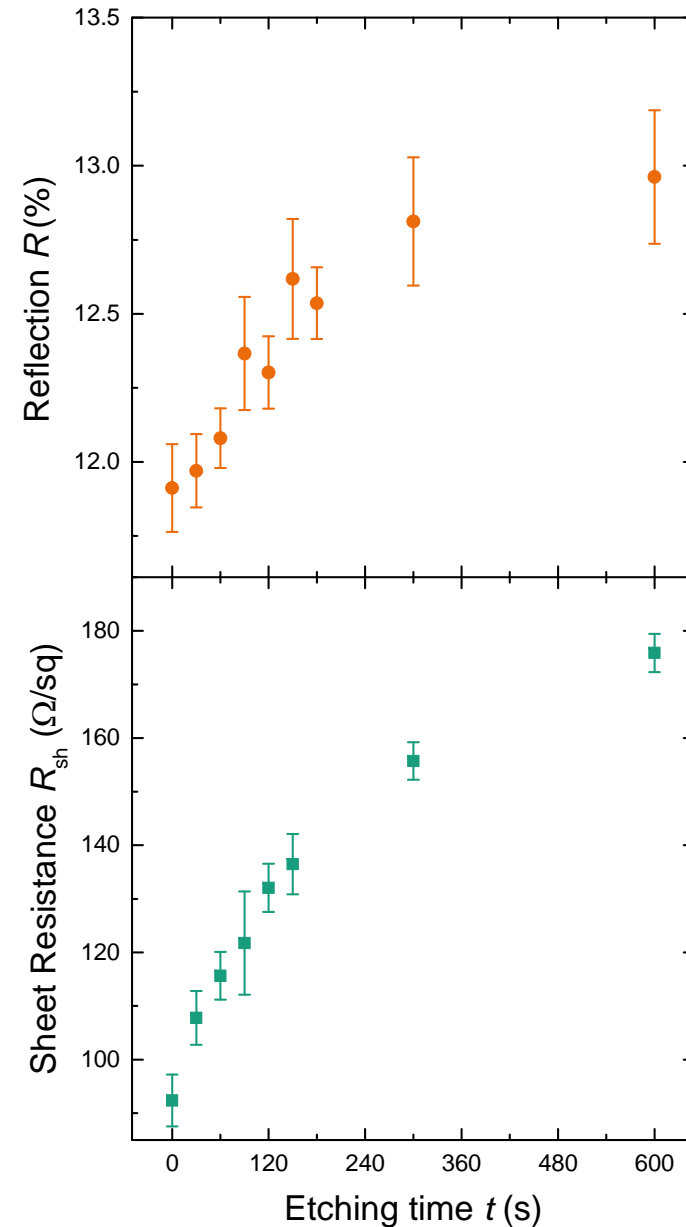




# Selective Emitter PERC

## *Reflection and sheet resistance*

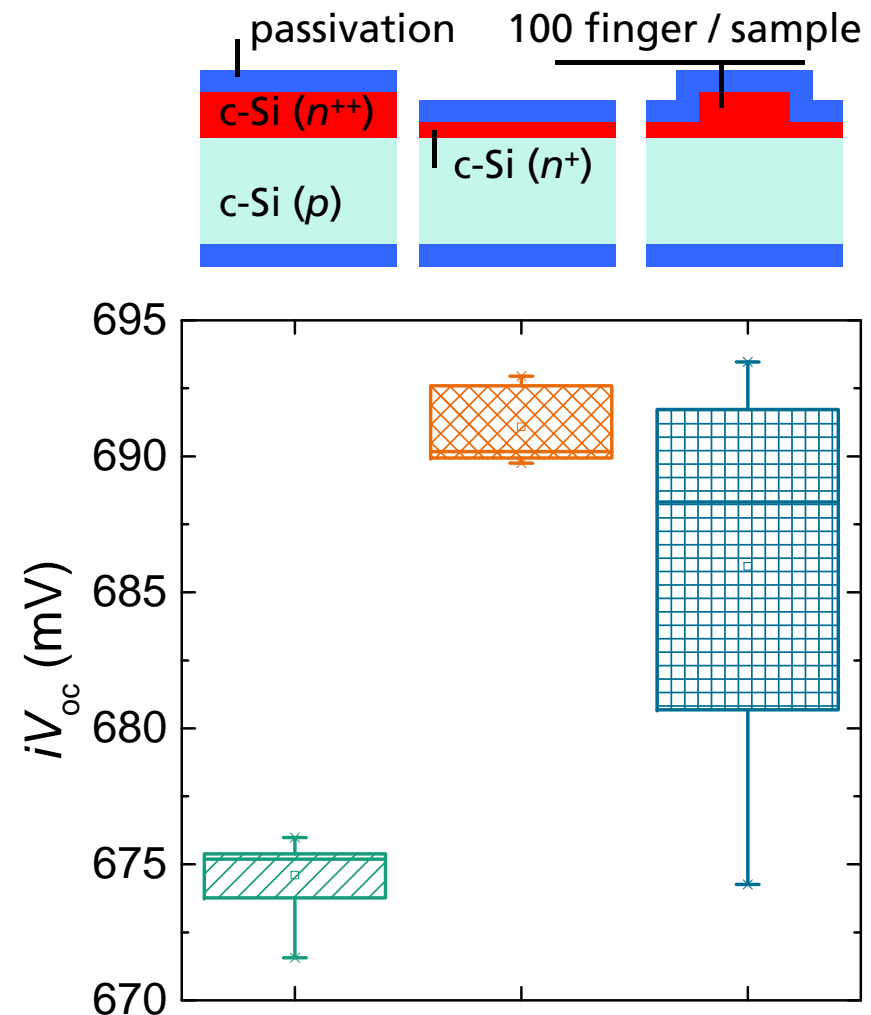
- Sheet resistance  $R_{sh}$  adjustable with etching time
- Minor increase in reflection due to rounding of pyramids' tips
- **Trade-off** between resistive and recombination losses at  **$R_{sh} = 120 \text{ } \Omega/\text{sq}$**



# Selective Emitter PERC

## Recombination

- Evaluation of recombination by QSSPC and unsymmetrical sampling
- Silicon etching improves implied open circuit voltage  $iV_{oc}$  by around **20 mV**
- Selective silicon etching leads to a decrease in homogeneity
- Interaction between ink and etching media assumed



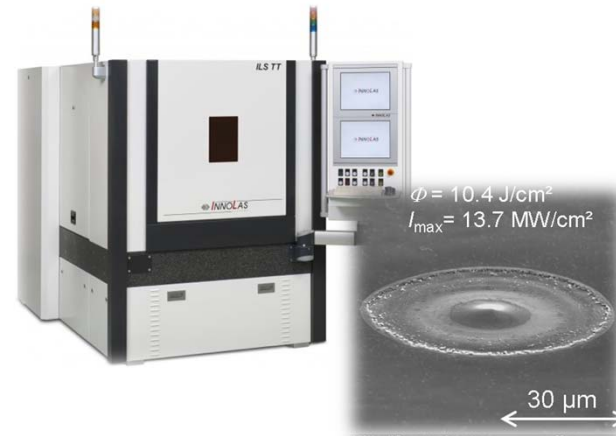
QSSPC: Quasy steady state photo conductance



## Application II (Industry)

### *Bifacial cells*

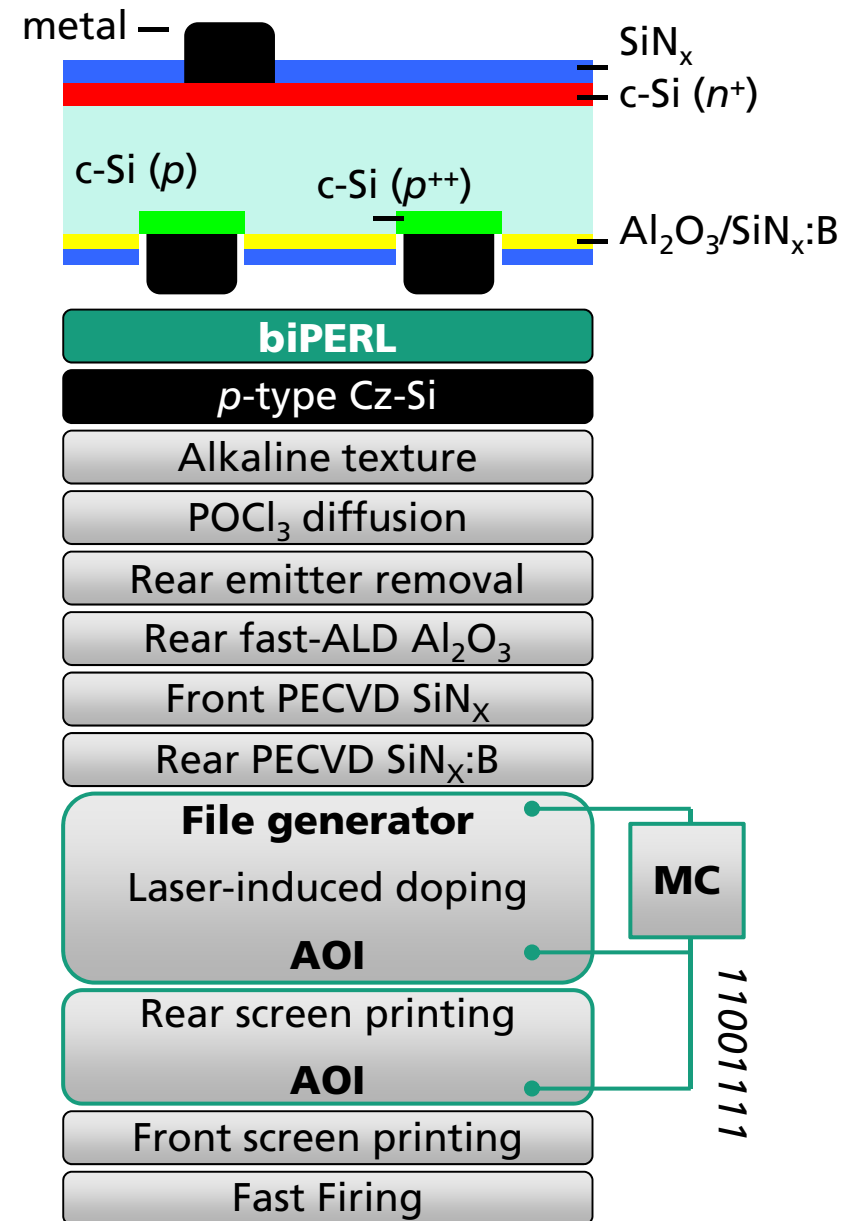
## Screen-printed metal on laser-induced doping (pPassDop) and Laser Contact Opening (LCO)



# Bifacial PERL

## Patterning

- Compatible with existing cell fabs
- Laser processing and screen printing **in a row**
- Compatible with hazardous failure of screen printers
- Doping patterning
- ***pPassDop***
  - Deposition of  $\text{Al}_2\text{O}_3/\text{SiN}_x\text{:B}$
  - Laser-induced Al/B doping



# Bifacial PERL

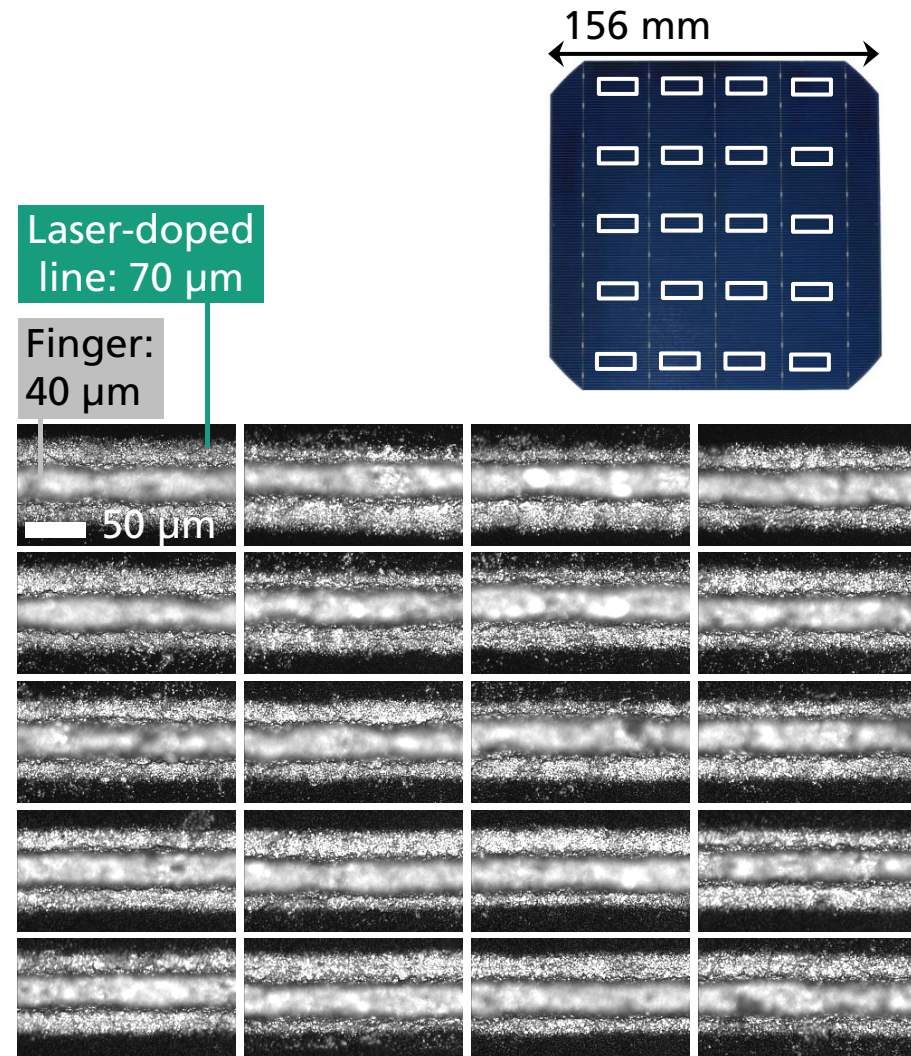
## *Alignment precision*

### ■ Method

- Laser writing of **adapted pattern**
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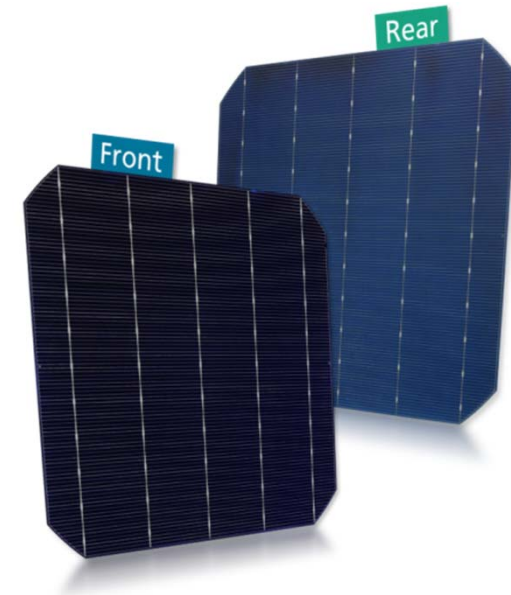
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E. Lohmüller et al., WCPEC, 2018

# Solar cell results



Type	Prec.	$V_{oc}$ (mV)	$J_{sc}$ (mA/cm <sup>2</sup> )	$FF$ (%)	$\eta_{front}$ (%)	$\eta_{rear}$ (%)	$\beta$ (%)	$p_{out}^*$ (mW/cm <sup>2</sup> )
monoPERC	ISE	667	40.2	80.7	21.6			21.6
biPERL [1]	ISE	651	39.2	79.9	20.4	18.0	88	22.2

\* $p_{out}$  for  $G_{front} = 100 \text{ mW/cm}^2$  (STC) and  $G_{rear} = 10 \text{ mW/cm}^2$ ;

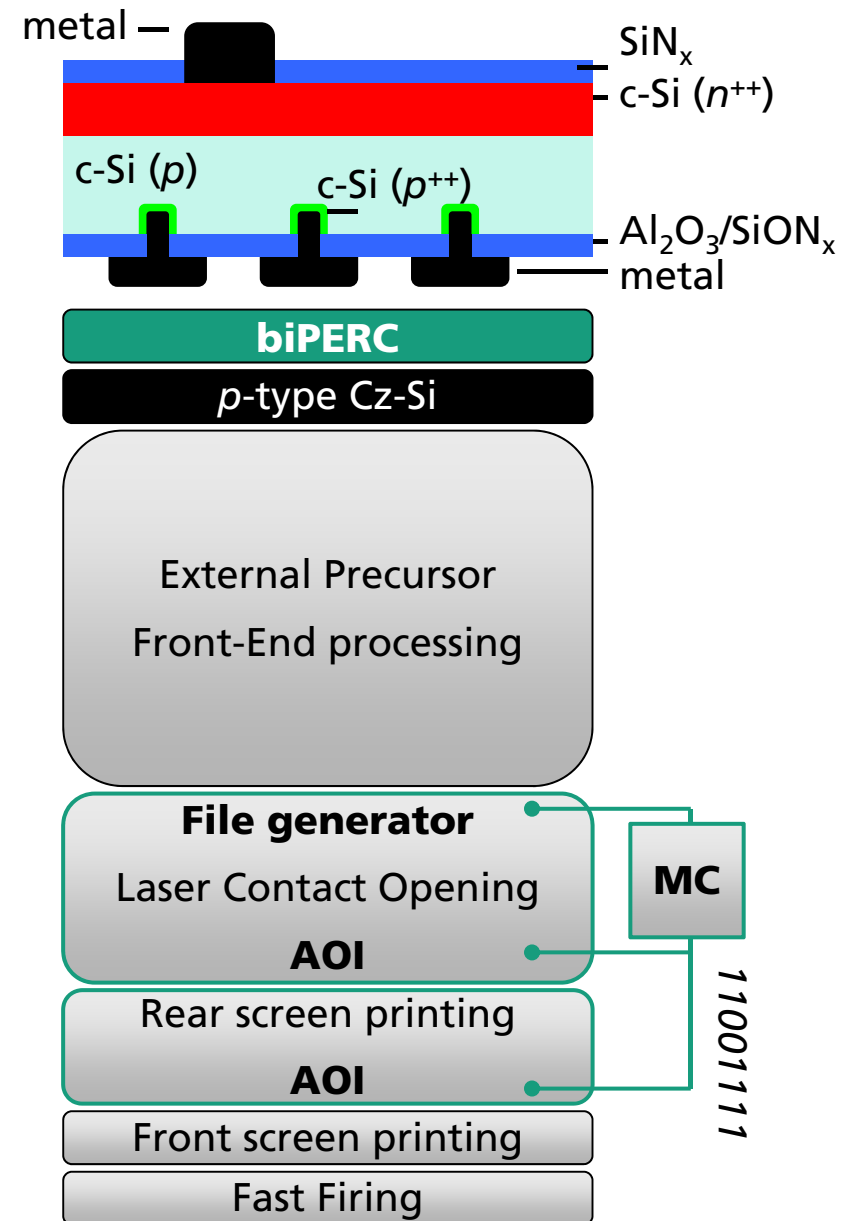
Conversion efficiencies measured on a black chuck;

[1] E. Lohmüller et al., WCPEC, 2018

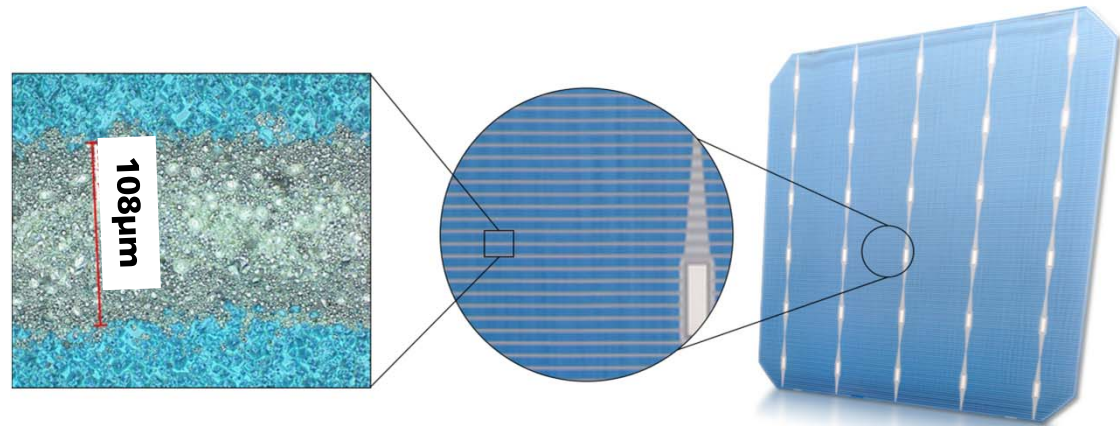
# Bifacial PERC

## Patterning

- LCO patterning
  - Laser processing
- Metal application
  - Screen printing
  - Al Paste (not firing-through)
- Contact formation
  - Fast Firing
  - Al-Si alloying



# Solar cell results



- Generally: method works stable on e.g. 100 μm Al on 30 μm LCO

Type	Prec.	$V_{oc}$ (mV)	$J_{sc}$ (mA/cm <sup>2</sup> )	FF (%)	$\eta_{front}$ (%)	$\eta_{rear}$ (%)	$\beta$ (%)	$p_{out}^*$ (mW/cm <sup>2</sup> )
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biPERL [1]	ISE	651	39.2	79.9	20.4	18.0	88	22.2
biPERC [2]	Yes	674	39.7	80.0	21.4	12.6	59	<b>22.7</b>

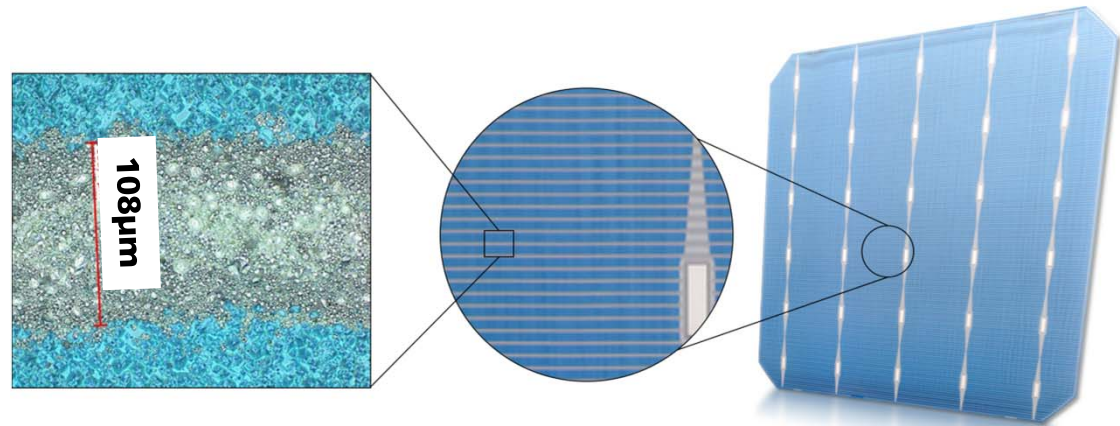
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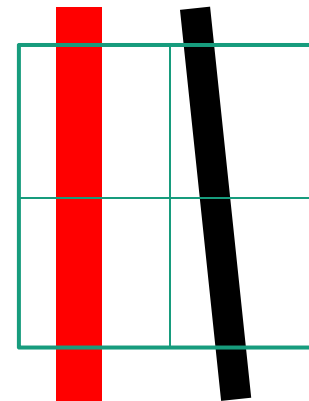
[1] E. Lohmüller et al., WCPEC, 2018; [2] T. Fellmeth et al., PV-SEC, 2017;



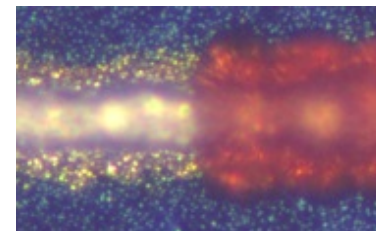
# Conclusion

- Digital method established for precise, shape-congruent patterning
  - Scalable with AOI
- High alignment accuracy of  $\pm 15 \mu\text{m}$  between different patterning methods
- Successful process integration
  - biPERL (*p*-type)
  - biPERC (*p*-type)

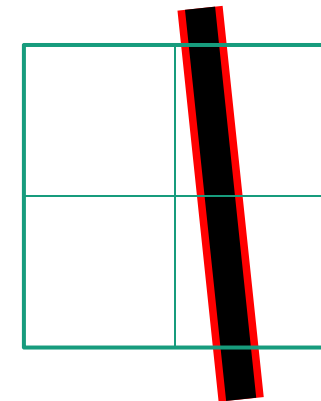
Initial



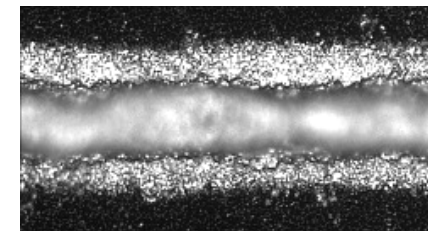
Ink - SP



Corrected



Laser - SP



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by the German Bundestag



# Thank you for your Attention!



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